PD- 93931

International
IOR Rectifier

PROVISIONAL

SMPS MOSFET

IRFBA34N50C

HEXFET® Power MOSFET

Applications
- Switch Mode Power Supply (SMPS)
- UninterruptIble Power Supply
- High Speed Power Switching

V_{DSS}	$R_{DS(on)}$ typ.	I_D
500V	**0.070Ω**	**40A**

Benefits
- Low Gate Charge Qg results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current

Super-220™

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	40	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	25	
I_{DM}	Pulsed Drain Current ①	160	
P_D @T_C = 25°C	Power Dissipation	310	W
	Linear Derating Factor	2.5	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Recommended clip force	20	N

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	480	mJ
I_{AR}	Avalanche Current①	—	34	A
E_{AR}	Repetitive Avalanche Energy①	—	31	mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.40	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	58	

6/2/00

Static @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.68	—	V/°C	Reference to 25°C, I_D = 1mA⑥
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.070	0.075	Ω	V_{GS} = 10V, I_D = 24A ④
$V_{GS(th)}$	Gate Threshold Voltage	3.5	—	5.5	V	V_{DS} = V_{GS}, I_D = 250µA
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	µA	V_{DS} = 500V, V_{GS} = 0V
		—	—	250		V_{DS} = 400V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -20V

Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	20	—	—	S	V_{DS} = 50V, I_D = 20A
Q_g	Total Gate Charge	—	190	—	nC	I_D = 20A
Q_{gs}	Gate-to-Source Charge	—	45	—		V_{DS} = 400V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	90	—		V_{GS} = 10V, ④
$t_{d(on)}$	Turn-On Delay Time	—	23	—	ns	V_{DD} = 250V
t_r	Rise Time	—	29	—		I_D = 20A
$t_{d(off)}$	Turn-Off Delay Time	—	55	—		R_G = 1.3Ω
t_f	Fall Time	—	6.3	—		V_{GS} = 10V, ④
C_{iss}	Input Capacitance	—	6330	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	3600	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	140	—		f = 1.0MHz
C_{oss}	Output Capacitance	—	15150	—		V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz
C_{oss}	Output Capacitance	—	140	—		V_{GS} = 0V, V_{DS} = 400V, f = 1.0MHz
C_{oss} eff.	Effective Output Capacitance	—	460	—		V_{GS} = 0V, V_{DS} = 0V to 400V ⑤

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	40	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	160		
V_{SD}	Diode Forward Voltage	—	—	1.5	V	T_J = 25°C, I_S = 24A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	510	770	ns	T_J = 125°C, I_F = 20A
Q_{rr}	Reverse RecoveryCharge	—	11	17	µC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

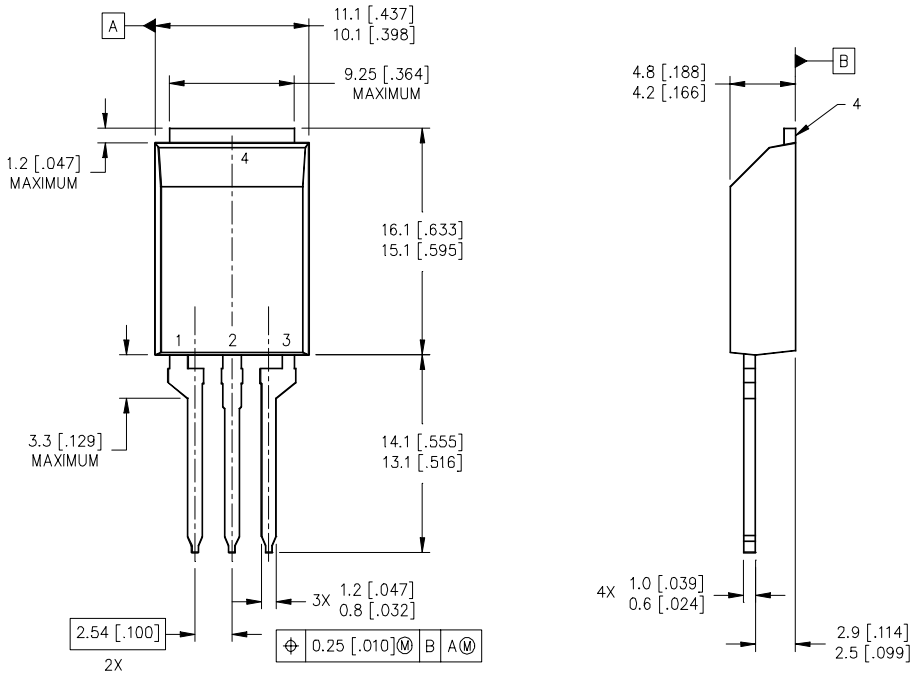
① Repetitive rating; pulse width limited by max. junction temperature.

② Starting T_J = 25°C, L = 0.83mH, R_G = 25Ω, I_{AS} = 34A,

③ I_{SD} ≤ 20A, di/dt ≤ 42A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150°C

④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

Super-220™ Package Outline



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M–1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-273AA.

LEAD ASSIGNMENTS

MOSFET	IGBT
1 – GATE	1 – GATE
2 – DRAIN	2 – COLLECTOR
3 – SOURCE	3 – EMITTER
4 – DRAIN	4 – COLLECTOR

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Data and specifications subject to change without notice. 6/00